**XPT IGBT** 

preliminary

1200 V  $V_{CES}$ 

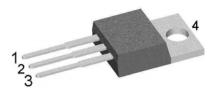
38A

V<sub>CE(sat)</sub> = 1.8V

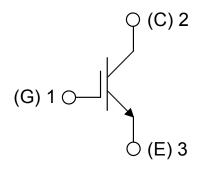
Single IGBT

Part number

IXA20I1200PB



Backside: collector



### Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10 µsec.
  - very low gate charge
- low EMI
- square RBSOA @ 3x Ic
- Thin wafer technology combined with the XPT design results in a competitive low VCE(sat)

### Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipmentSwitched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

### Package: TO-220

- · Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0





preliminary

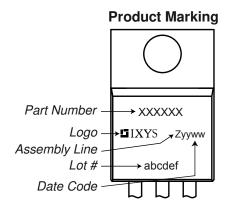
IGBT					1	Ratings	3	
Symbol	Definition		Conditions		min.	typ.	max.	Unit
V <sub>CES</sub>	collector emitter voltage			$T_{VJ} = 25^{\circ}C$			1200	V
V <sub>GES</sub>	max. DC gate voltage						±20	V
$V_{GEM}$	max. transient gate emitter voltage						±30	V
I <sub>C25</sub>	collector current			$T_{\rm C} = 25^{\circ}{\rm C}$			38	Α
I <sub>C80</sub>				$T_{c} = 80^{\circ}C$			22	Α
P <sub>tot</sub>	total power dissipation			$T_C = 25^{\circ}C$			165	W
V <sub>CE(sat)</sub>	collector emitter saturation voltage		$I_{C}$ = 15A; $V_{GE}$ = 15 V	$T_{VJ} = 25^{\circ}C$		1.8	2.1	V
				$T_{VJ} = 125$ °C		2.1		V
$V_{GE(th)}$	gate emitter threshold voltage		$I_C$ = 0.6mA; $V_{GE}$ = $V_{CE}$	$T_{VJ} = 25^{\circ}C$	5.4	5.9	6.5	V
I <sub>CES</sub>	collector emitter leakage current		$V_{CE} = V_{CES}$ ; $V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}C$			0.1	mA
				$T_{VJ} = 125$ °C		0.1		mΑ
I <sub>GES</sub>	gate emitter leakage current		$V_{GE} = \pm 20 \text{ V}$				500	nA
$Q_{G(on)}$	total gate charge		$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_{C} =$	15 A		47		nC
t <sub>d(on)</sub>	turn-on delay time	)				70		ns
tr	current rise time		2.1.28.1.1	T 40500		40		ns
$t_{d(off)}$	turn-off delay time		inductive load	$T_{VJ} = 125^{\circ}C$		250		ns
t <sub>f</sub>	current fall time	۲	$V_{CE} = 600 \text{ V}; I_{C} = 15 \text{ A}$			100		ns
E <sub>on</sub>	turn-on energy per pulse		$V_{GE} = \pm 15 \text{ V}; R_G = 56 \Omega$			1.65		mJ
E <sub>off</sub>	turn-off energy per pulse	J				1.7		mJ
RBSOA	reverse bias safe operating area	7	$V_{GE} = \pm 15 \text{ V}; R_{G} = 56 \Omega$	T <sub>VJ</sub> = 125°C				 
I <sub>CM</sub>			$V_{CEmax} = 1200 V$				45	Α
SCSOA	short circuit safe operating area	7	V <sub>CEmax</sub> = 900 V					 
tsc	short circuit duration	}	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V}$	$T_{VJ} = 125$ °C			10	μs
I <sub>sc</sub>	short circuit current	J	$R_G$ = 56 $\Omega$ ; non-repetitive			60		Α
R <sub>thJC</sub>	thermal resistance junction to case						0.76	K/W
R <sub>thCH</sub>	thermal resistance case to heatsink					0.50		K/W



# IXA20I1200PB

preliminary

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal			35	Α
T <sub>VJ</sub>	virtual junction temperature		-40		150	°C
T <sub>op</sub>	operation temperature		-40		125	°C
T <sub>stg</sub>	storage temperature		-40		150	°C
Weight				2		g
M <sub>D</sub>	mounting torque		0.4		0.6	Nm
F <sub>c</sub>	mounting force with clip		20		60	N



#### Part number

I = IGBT

X = XPT IGBTA = Gen 1 / std

20 = Current Rating [A]

I = Single IGBT

1200 = Reverse Voltage [V] PB = TO-220AB (3)

O	rdering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
St	tandard	IXA20I1200PB	IXA20I1200PB	Tube	50	507929

Similar Part	Package	Voltage class
IXA20IF1200HB	TO-247AD (3)	1200

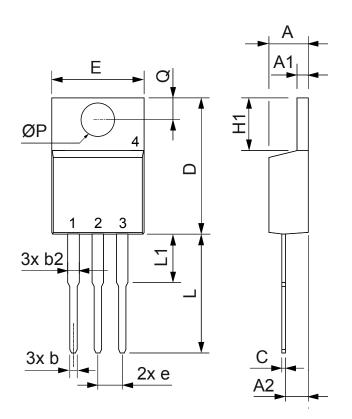
Equiva	lent Circuits for Simulation	* on die level	T <sub>VJ</sub> = 150 °C
$I \rightarrow V_0$	)—[R <sub>0</sub> ]—	IGBT	
V <sub>0 max</sub>	threshold voltage	1.1	V
R <sub>0 max</sub>	slope resistance *	86	$m\Omega$





preliminary

## Outlines TO-220



Dim.	Millimeter		Inches		
	Min.	Max.	Min.	Max.	
Α	4.32	4.82	0.170	0.190	
A1	1.14	1.39	0.045	0.055	
A2	2.29	2.79	0.090	0.110	
b	0.64	1.01	0.025	0.040	
b2	1.15	1.65	0.045	0.065	
С	0.35	0.56	0.014	0.022	
D	14.73	16.00	0.580	0.630	
E	9.91	10.66	0.390	0.420	
е	2.54	BSC	0.100	BSC	
H1	5.85	6.85	0.230	0.270	
L	12.70	13.97	0.500	0.550	
L1	2.79	5.84	0.110	0.230	
ØP	3.54	4.08	0.139	0.161	
Q	2.54	3.18	0.100	0.125	

